

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S22	306	257/725.ccls. and @ad<"20031030"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 21:51
S23	232	257/758.ccls. and @ad<"20031030" and dummy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 21:54
S24	829	438/669.ccls. and @ad<"20031030"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 21:55
S25	19	438/669.ccls. and @ad<"20031030" and dummy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 21:55
S26	116	438/926.ccls. and @ad<"20031030" and dummy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 21:56
S27	1137	semiconductor and (wiring or conductor or electrode) and @ad<"20031030" and (dummy with (pattern\$3 or structure or layer or wiring)) and (CMP or polish\$4 or damascene) and (cvd or vapor adj deposition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/09 21:59